GMBT2411

NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

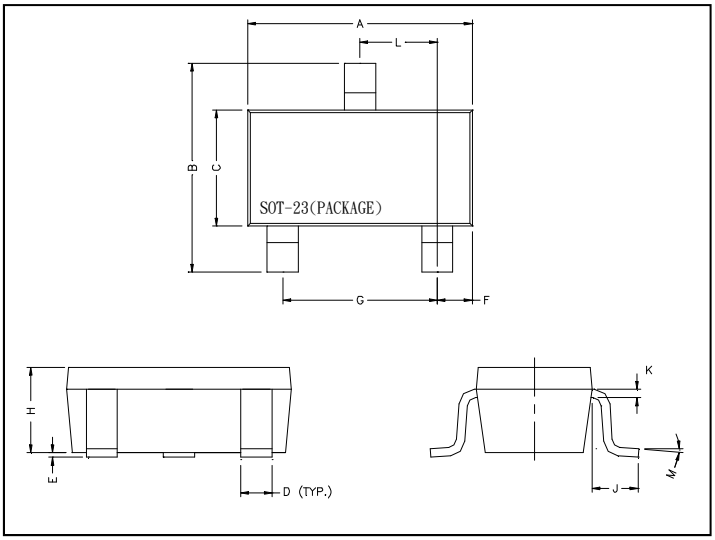
Description

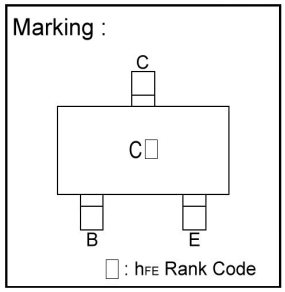
The GMBT2411 is designed for medium power amplifier applications.

Features

- $I_{CMax.}$=500mA
- Low $V_{CE(sat).}$ Optimal for low voltage operation.
- Complementary to GMBT1036

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_D	225	mW

Electrical Characteristics (Ta = 25℃, unless otherwise stated)

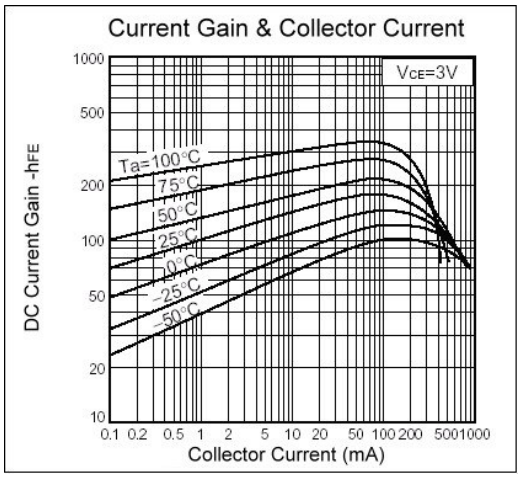
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	40	-	-	V	I_C=100uA , I_E=0
BV_{CEO}	32	-	-	V	I_C=1mA, I_B=0
BV_{EBO}	5	-	-	V	I_E=100uA ,I_C=0
I_{CBO}	-	-	1	uA	V_{CB}=20V, I_E=0
I_{EBO}	-	-	1	uA	V_{EB}=4V, I_C=0
*$V_{CE(sat)}$	-	-	400	mV	I_C=500mA, I_B=50mA
*h_{FE}	82	-	390		V_{CE}=3V, I_C=100mA
fT	-	250	-	MHz	V_{CE}=5V, I_E=-20mA, f=100MHz
Cob	-	6	-	pF	V_{CB}=10V, I_E=0, f=1MHz

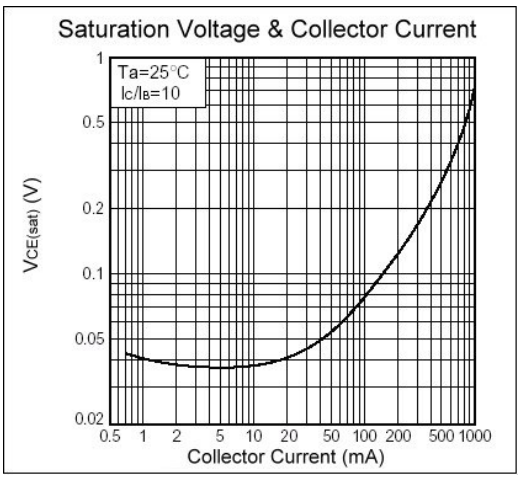
*Measured under pulse condition. Pulse width=300μs, Duty Cycle≦2%

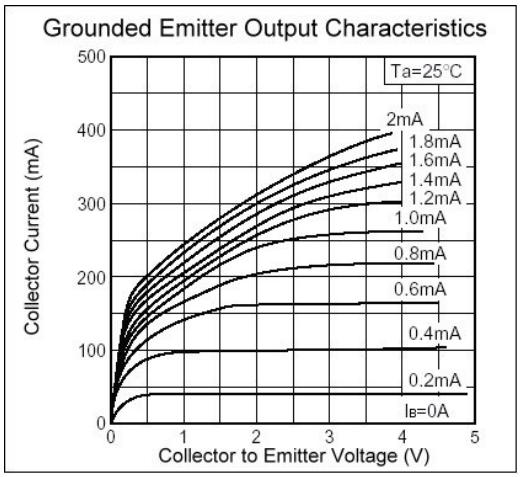
Classification Of h_{FE}

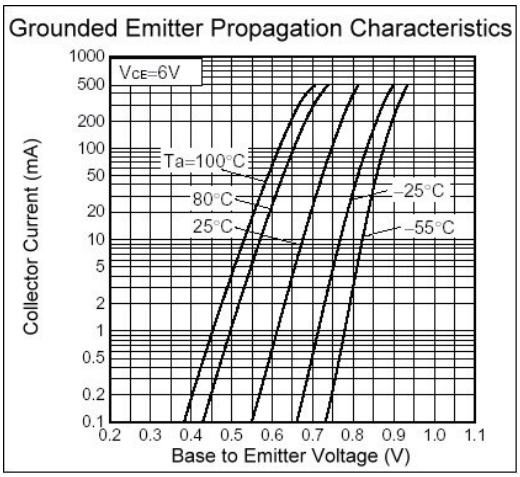
Rank	CP	CQ	CR
Range	82 - 180	120 - 270	180 - 390

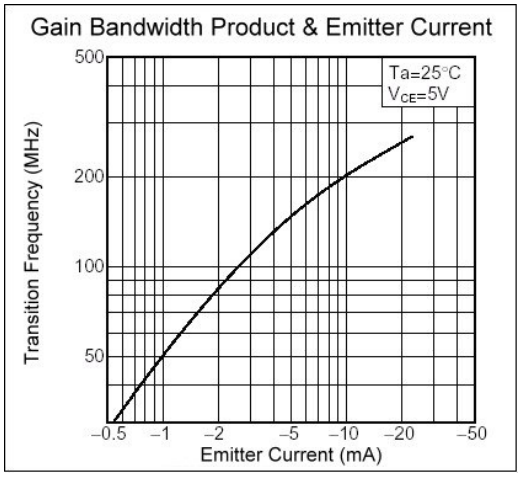
Characteristics Curve

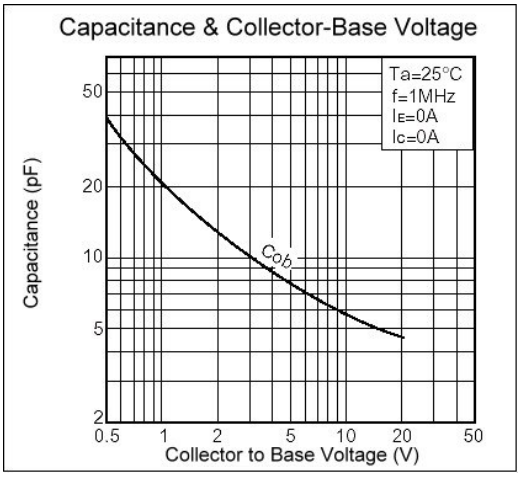












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